

### General Description

The AAT9125 30V N-Channel Power MOSFET is a member of AnalogicTech's TrenchDMOS™ product family. Using the ultra-high density proprietary TrenchDMOS technology, this product demonstrates high power handling and small size.

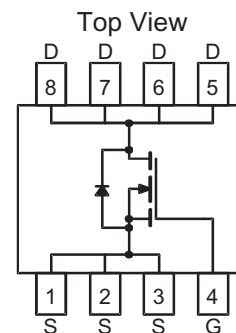
### Features

- $V_{DS(MAX)} = 30V$
- $I_{D(MAX)} = 12.5A @ 25^{\circ}C$
- Low  $R_{DS(ON)}$ :
  - $9 m\Omega @ V_{GS} = 10V$
  - $14 m\Omega @ V_{GS} = 4.5V$

### Applications

- DC-DC converters for mobile CPUs
- Battery-powered portable equipment
- High power density switch-mode supplies
- Point-of-use Power Supplies

### SOP8 Package



### Absolute Maximum Ratings ( $T_A=25^{\circ}C$ unless otherwise noted)

| Symbol         | Description   | Value               | Units       |   |
|----------------|---|---------------------|-------------|---|
| $V_{DS}$       | Drain-Source Voltage  | 30                  | V           |   |
| $V_{GS}$       | Gate-Source Voltage   | $\pm 20$            |             |   |
| $I_D$          | Continuous Drain Current @ $T_J=150^{\circ}C$ <sup>1</sup>  | $T_A = 25^{\circ}C$ | $\pm 12.5$  | A |
|                |   | $T_A = 70^{\circ}C$ | $\pm 10$    |   |
| $I_{DM}$       | Pulsed Drain Current  | $\pm 52$            |             |   |
| $I_S$          | Continuous Source Current (Source-Drain Diode) <sup>1</sup> | 2.25                |             |   |
| $P_D$          | Maximum Power Dissipation <sup>1</sup>                      | $T_A = 25^{\circ}C$ | 2.5         | W |
|                |   | $T_A = 70^{\circ}C$ | 1.6         |   |
| $T_J, T_{STG}$ | Operating Junction and Storage Temperature Range            | -55 to 150          | $^{\circ}C$ |   |

### Thermal Characteristics

| Symbol          | Description                              | Value | Units         |
|-----------------|--|-------|---------------|
| $R_{\theta JA}$ | Typical Junction-to-Ambient <sup>1</sup> | 50    | $^{\circ}C/W$ |
| $R_{\theta JC}$ | Typical Junction-to-Case                 | 25    | $^{\circ}C/W$ |

Note 1: Mounted on 1" x 1" FR4 Copper Board, 10 sec pulse width

### Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

| Symbol                                      | Description                               | Conditions   | Min | Typ         | Max     | Units |
|---|---|--|-----|-------------|---------|-------|
| <b>DC Characteristics</b>                   |   |  |     |             |         |       |
| BV <sub>DSS</sub>                           | Drain-Source Breakdown Voltage            | V <sub>GS</sub> =0V, I <sub>D</sub> =250μA   | 30  |             |         | V     |
| R <sub>DS(ON)</sub>                         | Drain-Source ON-Resistance <sup>2</sup>   | V <sub>GS</sub> =10V, I <sub>D</sub> =12A<br>V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A                      |     | 7.5<br>11.5 | 9<br>14 | mΩ    |
| I <sub>D(ON)</sub>                          | On-State Drain Current <sup>2</sup>       | V <sub>GS</sub> =10V, V <sub>DS</sub> =5V (Pulsed)   | 52  |             |         | A     |
| V <sub>GS(th)</sub>                         | Gate Threshold Voltage                    | V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250μA   | 1.0 |             |         | V     |
| I <sub>GSS</sub>                            | Gate-Body Leakage Current                 | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V   |     |             | ±100    | nA    |
| I <sub>DSS</sub>                            | Drain Source Leakage Current              | V <sub>GS</sub> =0V, V <sub>DS</sub> =30V<br>V <sub>GS</sub> =0V, V <sub>DS</sub> =30V, T <sub>J</sub> =55°C |     |             | 1<br>5  | μA    |
| g <sub>fs</sub>                             | Forward Transconductance <sup>2</sup>     | V <sub>DS</sub> =15V, I <sub>D</sub> =12.5A  |     | 30          |         | S     |
| <b>Dynamic Characteristics <sup>3</sup></b> |   |  |     |             |         |       |
| Q <sub>G</sub>                              | Total Gate Charge                         | V <sub>DS</sub> =15V, I <sub>D</sub> =12.5A, V <sub>GS</sub> =5V   |     | 31          | 50      | nC    |
| Q <sub>GT</sub>                             | Total Gate Charge                         | V <sub>DS</sub> =15V, I <sub>D</sub> =12.5A, V <sub>GS</sub> =10V  |     | 60          | 100     | nC    |
| Q <sub>GS</sub>                             | Gate-Source Charge                        | V <sub>DS</sub> =15V, I <sub>D</sub> =12.5A, V <sub>GS</sub> =10V  |     | 10          |         | nC    |
| Q <sub>GD</sub>                             | Gate-Drain Charge                         | V <sub>DS</sub> =15V, I <sub>D</sub> =12.5A, V <sub>GS</sub> =10V  |     | 9           |         | nC    |
| t <sub>D(ON)</sub>                          | Turn-ON Delay                             | V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>D</sub> =1.2Ω, R <sub>G</sub> =6Ω                         |     | 20          | 35      | ns    |
| t <sub>R</sub>                              | Turn-ON Rise Time                         | V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>D</sub> =1.2Ω, R <sub>G</sub> =6Ω                         |     | 14          | 30      | ns    |
| t <sub>D(OFF)</sub>                         | Turn-OFF Delay                            | V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>D</sub> =1.2Ω, R <sub>G</sub> =6Ω                         |     | 100         | 160     | ns    |
| t <sub>F</sub>                              | Turn-OFF Fall Time                        | V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>D</sub> =1.2Ω, R <sub>G</sub> =6Ω                         |     | 38          | 80      | ns    |
| <b>Source-Drain Diode Characteristics</b>   |   |  |     |             |         |       |
| V <sub>SD</sub>                             | Source-Drain Forward Voltage <sup>2</sup> | V <sub>GS</sub> =0, I <sub>S</sub> =2.25A  |     |             | 1.1     | V     |
| I <sub>S</sub>                              | Continuous Diode Current                  | T <sub>A</sub> =25°C   |     |             | 2.25    | A     |

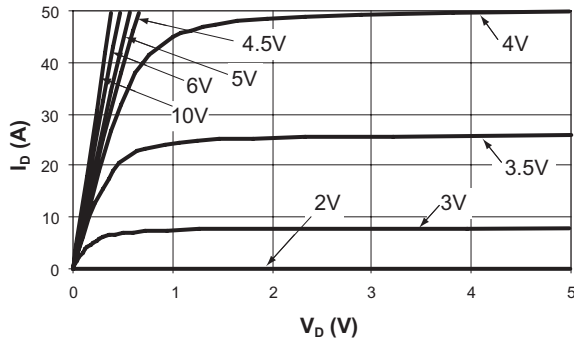
Note 2: Pulse test: Pulse Width = 300μs

Note 3: Guaranteed by design. Not subjected to production testing.

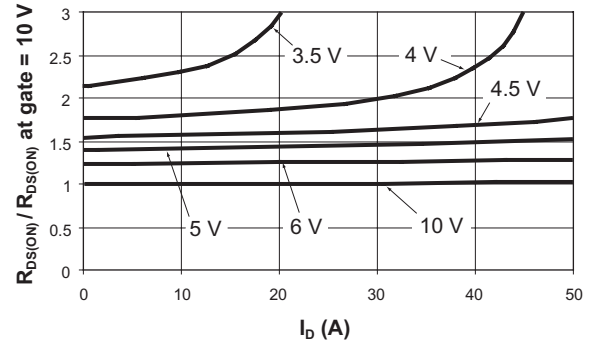
### Typical Characteristics

( $T_J = 25^\circ\text{C}$  unless otherwise noted)

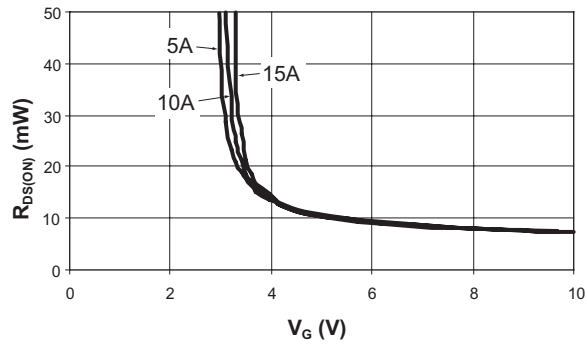
**Forward Characteristics**



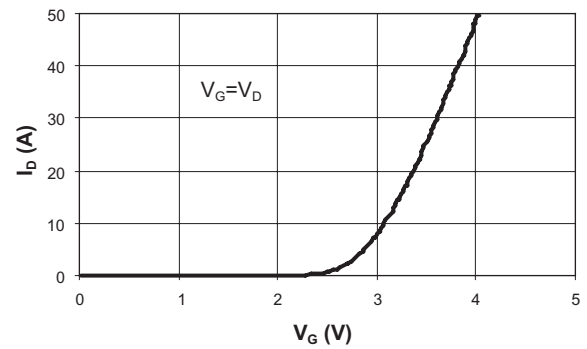
**Normalized  $R_{DS(ON)}$**



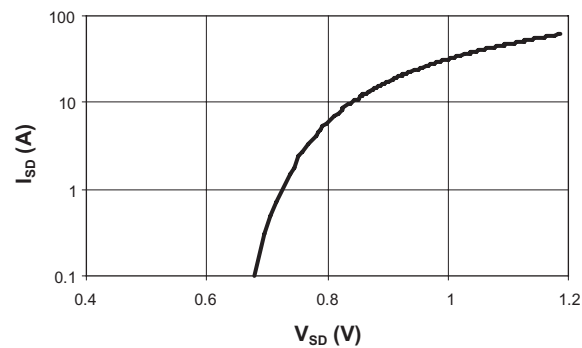
**$R_{DS(ON)}$  vs.  $V_G$**



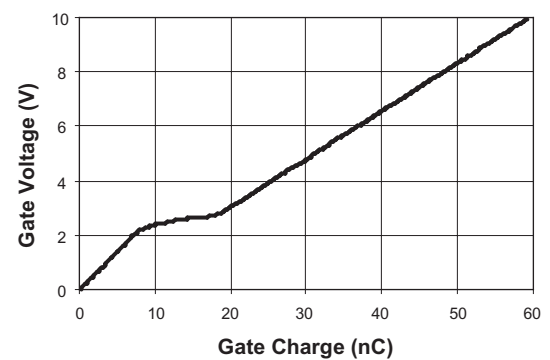
**Transfer**



**Source to Drain Voltage**



**Gate Charge Characteristics**

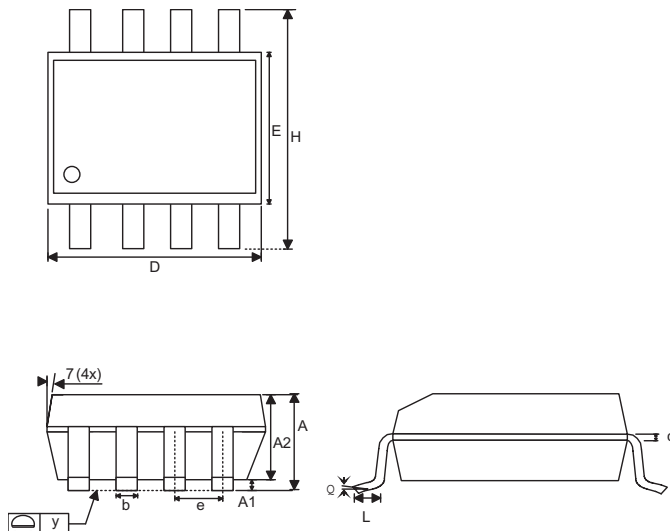


### Ordering Information

| Package | Marking | Part Number   |               |
|---------|---------|---------------|---------------|
|         |         | Bulk          | Tape and Reel |
| SOP-8   |         | AAT9125IAS-B1 | AAT9125IAS-T1 |

### Package Information

#### SOP-8



| Dim        | Millimeters |      | Inches |       |
|------------|-------------|------|--------|-------|
|            | Min         | Max  | Min    | Max   |
| A          | 1.35        | 1.75 | 0.053  | 0.069 |
| A1         | 0.10        | 0.25 | 0.004  | 0.010 |
| A2         | 1.45        |      | 0.057  |       |
| B          | 0.33        | 0.51 | 0.013  | 0.020 |
| C          | 0.19        | 0.25 | 0.007  | 0.010 |
| D          | 4.80        | 5.00 | 0.189  | 0.197 |
| E          | 3.80        | 4.00 | 0.150  | 0.157 |
| e          | 1.27        |      | 0.050  |       |
| H          | 5.80        | 6.20 | 0.228  | 0.244 |
| L          | 0.40        | 1.27 | 0.016  | 0.050 |
| Y          | 0.00        | 0.10 | 0.000  | 0.004 |
| $\theta 1$ | 0°          | 8°   | 0°     | 8°    |

Note:

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.
2. TOLERANCE 0.1000mm (4mil) UNLESS OTHERWISE SPECIFIED
3. COPLANARITY: 0.1000mm
4. DIMENSION L IS MEASURED IN GAGE PLANE.
5. CONTROLLING DIMENSION IS MILLIMETER; CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.